

SILICON PHOTODIODE VTP1332

FEATURES

- Low dark current
- Fast response
- Infrared transmitting/visible blocking spectral range
- Low junction capacitance

PRODUCT DESCRIPTION

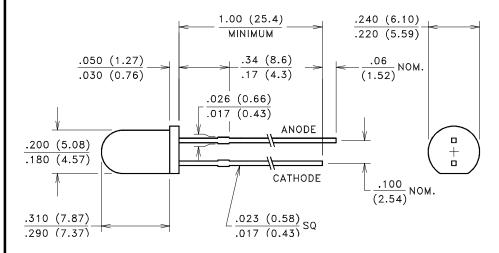
This VTP processed P on N planar silicon photodiode is housed in an IR transmitting, T-1 3/4 endlooking package.

These diodes exhibit low dark current under reverse bias. The VTP process offers low capacitance, resulting in fast response times.

ELECTRO-OPTICAL CHARACTERISTICS @ 25° C

| PARAMETER | SYMBOL | MIN. | TYP. | MAX. | UNITS |
|--|------------------|-------|-------|------|------------------------|
| SHORT CIRCUIT CURRENT @ 100 fc, 2850 K | Isc | 75 | | | μΑ |
| RESPONSIVITY @ 880 nm | R _e | 0.050 | 0.065 | | A/(W/cm ²) |
| DARK CURRENT @ V _R = 10 V | I _D | | | 25 | nA |
| REVERSE BREAKDOWN VOLTAGE @ 100 μA | V_{BR} | 30 | | | V |
| JUNCTION CAPACITANCE @ V _R = 0 V, 1 MHz | CJ | | | 100 | pF |
| ANGULAR RESPONSE (50% RESPONSE POINT) | θ _{1/2} | | ±20 | | Degrees |

PACKAGE DIMENSIONS inch (mm)



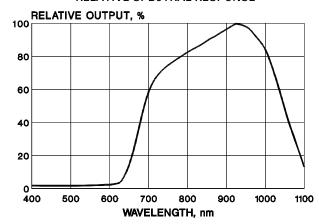
CASE 26 T-1 3/4 CHIP SIZE: .075 x .075 (1.90 x 1.90) TOTAL EXPOSED AREA: .0036 in² (2.326 mm²)

GENERAL CHARACTERISTICS

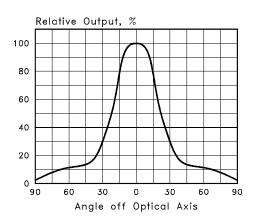
| PARAMETER | SYMBOL | TYPICAL RATING | UNITS |
|---|---------------------------------|------------------------|----------------------------|
| OPEN CIRCUIT VOLTAGE @ 100 fc, 2850 K SOURCE | Voc | 420 | mV |
| PEAK SPECTRAL RESPONSE @ 25°C | $\lambda_{\sf pk}$ | 920 | nm |
| SPECTRAL APPLICATION RANGE | λ_{range} | 725 - 1100 | nm |
| RISE/FALL TIMES @ 800 nm, V_R =10 V, R_L = 50 Ω | t _R / t _F | 20 | ns |
| TEMPERATURE COEFFICIENT SHORT CIRCUIT CURRENT @ 2850 K SOURCE DARK CURRENT @ V _R = 10 V OPEN CIRCUIT VOLTAGE | TC Isc TC Ib TC voc | +0.20 +11.0 -2.0 | % / °C % / °C mV/ °C |
| TEMPERATURE RANGE, OPERATING & STORAGE | Тамв | – 40 to +100 | °C |

TYPICAL CHARACTERISTIC CURVES

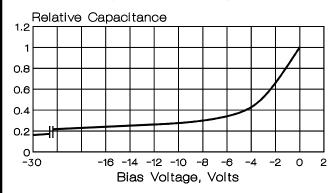
RELATIVE SPECTRAL RESPONSE



ANGULAR RESPONSE



RELATIVE JUNCTION CAPACITANCE vs BIAS VOLTAGE (REFERRED TO ZERO BIAS)



Specifications subject to change without prior notice. Information supplied by Excelitas Technologies is believed to be reliable, however, no responsibility is assumed for possible inaccuracies or omissions. The user should determine the suitability of this product in his own application. No patent rights are granted to any devices or circuits described herein.